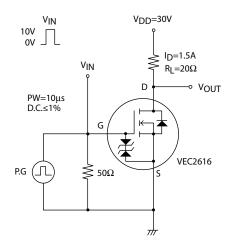
## **ELECTRICAL CHARACTERISTICS** at $Ta = 25^{\circ}C$ (Note 2)

Parameter	Symbol	Conditions	Value			Unit
	- ,		min	typ	max	0
[N-Channel]	1					
Drain to Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	60			V
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V	_		1	μA
Gate to Source Leakage Current	IGSS	V <sub>GS</sub> =±16V, V <sub>DS</sub> =0V	_		±10	μA
Gate Threshold Voltage	VGS(th)	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	1.2		2.6	V
Forward Transconductance	sconductance gFS V <sub>DS</sub> =10V, I <sub>D</sub> =1.5A			2.6		S
Static Drain to Source On-State Resistance	R <sub>DS</sub> (on)1	ID=1.5A, VGS=10V		62	80	mΩ
	R <sub>DS</sub> (on)2	I <sub>D</sub> =0.75A, V <sub>GS</sub> =4.5V		76	106	mΩ
	R <sub>DS</sub> (on)3	I <sub>D</sub> =0.75A, V <sub>GS</sub> =4V		83	116	mΩ
Input Capacitance	Ciss			505		pF
Output Capacitance	Coss	V <sub>DS</sub> =20V, f=1MHz		57		pF
Reverse Transfer Capacitance	Crss			37		pF
Turn-ON Delay Time	t <sub>d</sub> (on)			7.3		ns
Rise Time	tr			7.5		ns
Turn-OFF Delay Time	t <sub>d</sub> (off)	See specified Test Circuit		41		ns
Fall Time	tf			22		ns
Total Gate Charge	Qg			10		nC
Gate to Source Charge	Qgs	V <sub>DS</sub> =30V, V <sub>GS</sub> =10V, I <sub>D</sub> =3A		1.6		nC
Gate to Drain "Miller" Charge	Qgd			2.1		nC
Forward Diode Voltage	V <sub>SD</sub>	IS=3A, VGS=0V		0.81	1.2	V
[P-Channel]						
Drain to Source Breakdown Voltage	V(BR)DSS	ID=-1mA, VGS=0V	-60			V
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =-60V, V <sub>GS</sub> =0V			-1	μA
Gate to Source Leakage Current	IGSS	V <sub>GS</sub> =±16V, V <sub>DS</sub> =0V			±10	μA
Gate Threshold Voltage	VGS(th)	V <sub>DS</sub> =-10V, I <sub>D</sub> =-1mA	-1.2		-2.6	V
Forward Transconductance	9FS	V <sub>DS</sub> =-10V, I <sub>D</sub> =-1.5A		3.9		S
Static Drain to Source On-State Resistance	R <sub>DS</sub> (on)1	ID=-1.5A, VGS=-10V		105	137	mΩ
	R <sub>DS</sub> (on)2	ID=-0.75A, VGS=-4.5V		128	180	mΩ
	R <sub>DS</sub> (on)3	ID=-0.75A, VGS=-4V		138	194	mΩ
Input Capacitance	Ciss			420		pF
Output Capacitance	Coss	V <sub>DS</sub> =–20V, f=1MHz		54		pF
Reverse Transfer Capacitance	Crss			44		pF
Turn-ON Delay Time	t <sub>d</sub> (on)			6.4		ns
Rise Time	tr			9.8		ns
Turn-OFF Delay Time	t <sub>d</sub> (off)	See specified Test Circuit		65		ns
Fall Time	tf	1		36		ns
Total Gate Charge	Qg			11		nC
Gate to Source Charge	Qgs	VDS=-30V, VGS=-10V, ID=-2.5A		1.4		nC
Gate to Drain "Miller" Charge	Qgd			2		nC
Forward Diode Voltage	VSD	IS=-2.5A, VGS=0V		-0.83	-1.2	V

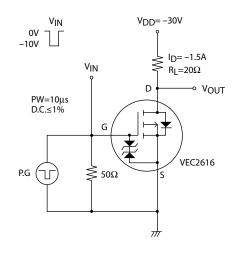
Note 2 : Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

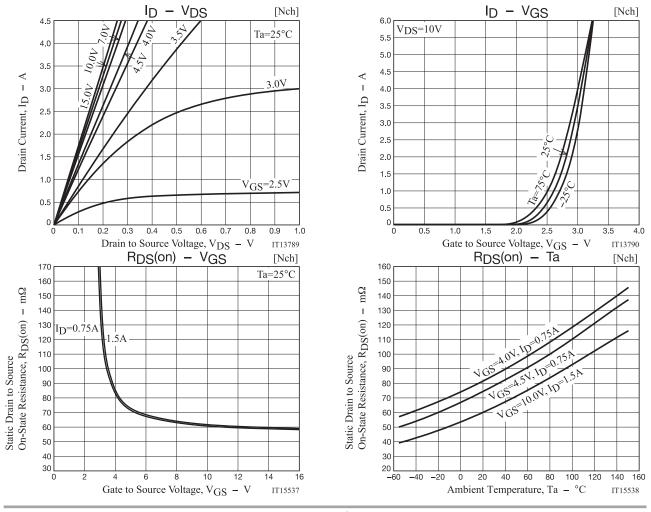
### **VEC2616**

# Switching Time Test Circuit [N-Channel]

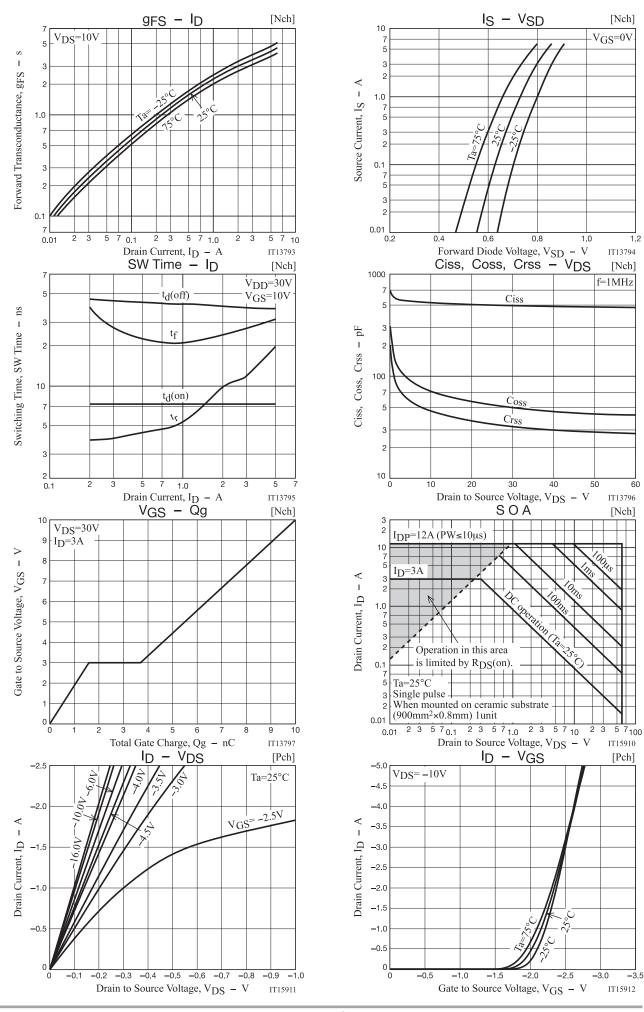


### [P-Channel]





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[Pch]

IT15914

[Pch]

V<sub>GS</sub>=0V

-1.0

-1.2

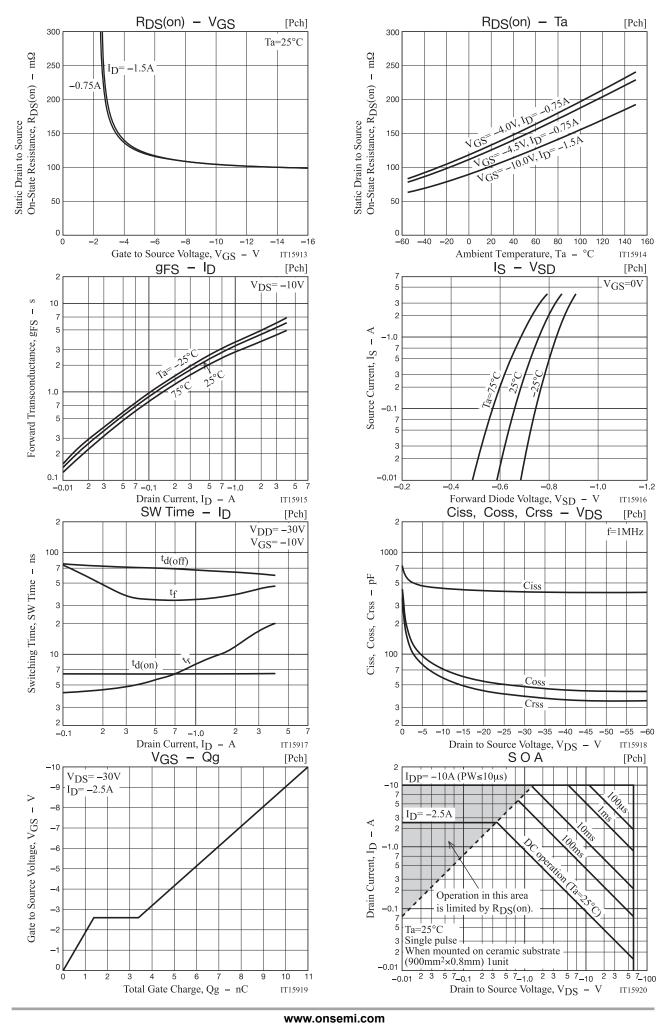
IT15916

[Pch]

IT15918

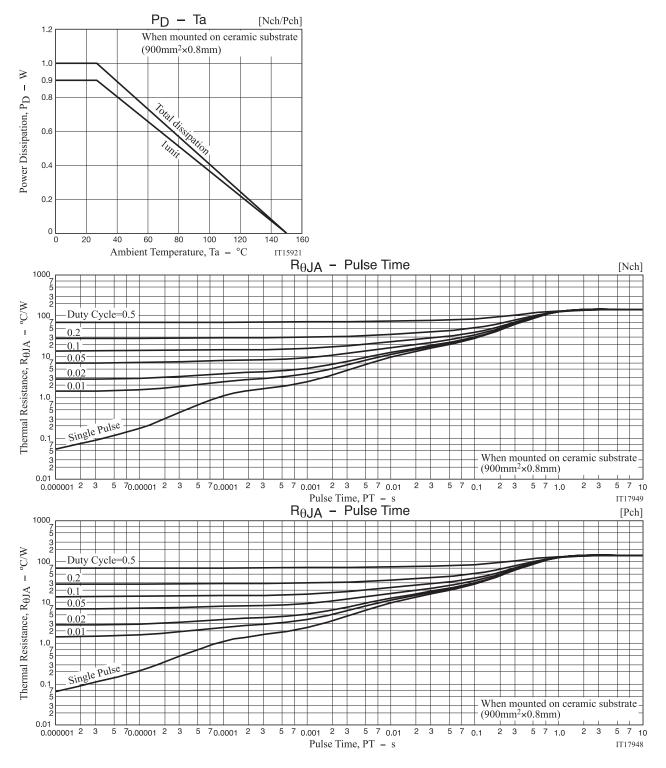
[Pch]

f=1MHz



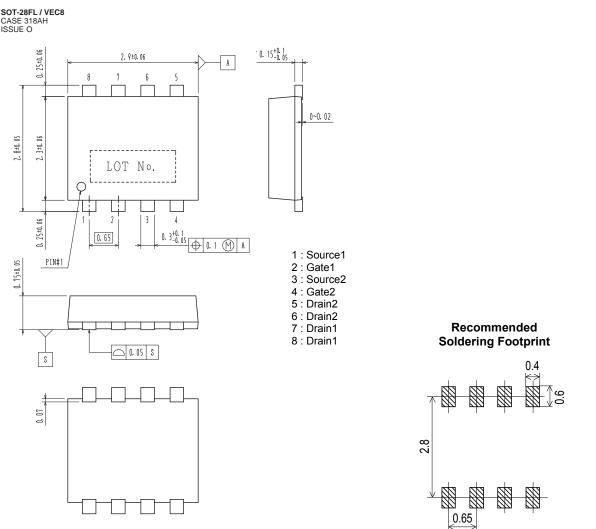
Downloaded from Arrow.com.

5



## PACKAGE DIMENSIONS

#### unit : mm



### **ORDERING INFORMATION**

Device	Marking	Package	Shipping (Qty / Packing)	
VEC2616-TL-H		SOT-28FL / VEC8	3,000 / Tape & Reel	
VEC2616-TL-W	UP	(Pb-Free / Halogen Free)		

† For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. http://www.onsemi.com/pub\_link/Collateral/BRD8011-D.PDF

# Note on usage : Since the VEC2616 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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